

Front Side Data

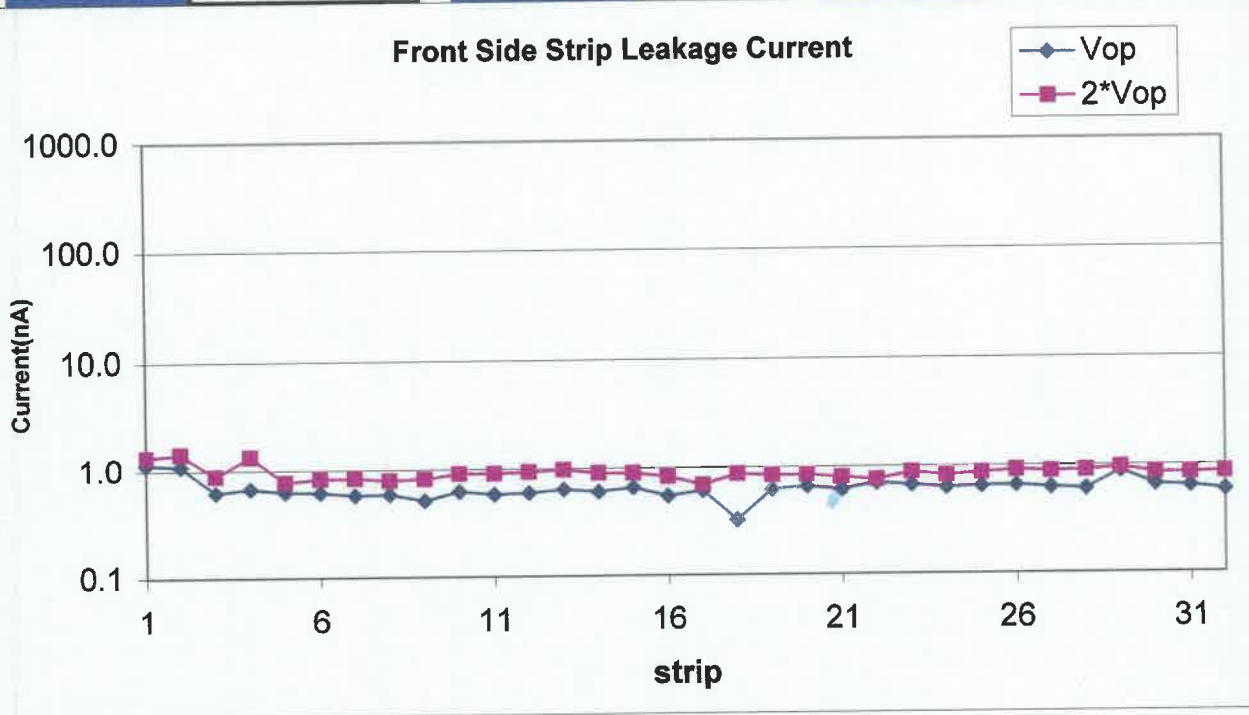
Wafer No.: **2435-2**

Thickness: **61** um

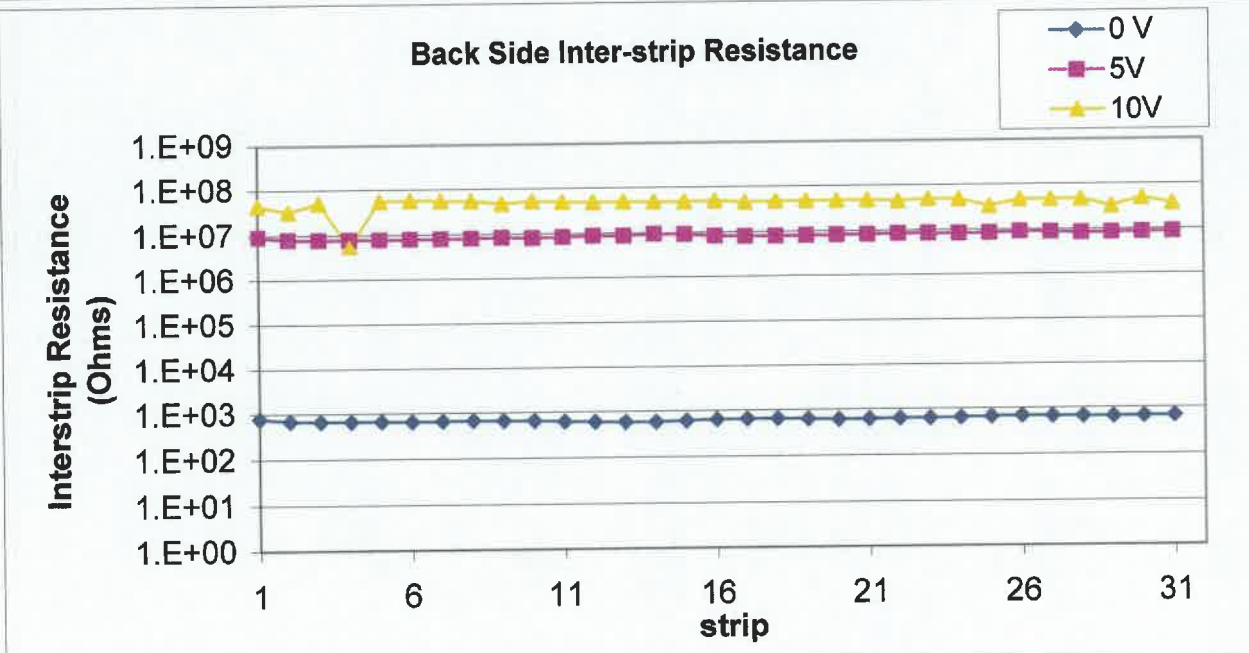
Vop: **5** Volts

Back Side Data

Strip	Current(nA)	
	Vop	2*Vop
1	1.15	1.34
2	1.10	1.44
3	0.63	0.89
4	0.68	1.35
5	0.63	0.78
6	0.62	0.83
7	0.58	0.84
8	0.59	0.80
9	0.52	0.83
10	0.62	0.92
11	0.58	0.92
12	0.60	0.95
13	0.64	0.98
14	0.61	0.91
15	0.66	0.90
16	0.55	0.84
17	0.61	0.70
18	0.32	0.88
19	0.61	0.85
20	0.66	0.84
21	0.62	0.80
22	0.70	0.76
23	0.67	0.89
24	0.63	0.82
25	0.65	0.87
26	0.66	0.92
27	0.63	0.89
28	0.61	0.90
29	0.99	0.85
30	0.66	0.86
31	0.64	0.85
32	0.59	0.87
Total	20.98	29.04



Strip	Back Resistance (Ω)		
	0V	5V	10V
1	7.9E+02	9.3E+06	4.6E+07
2	6.9E+02	8.1E+06	3.4E+07
3	6.6E+02	7.9E+06	5.2E+07
4	6.7E+02	7.9E+06	5.7E+06
5	6.7E+02	7.9E+06	5.7E+07
6	6.5E+02	8.1E+06	5.9E+07
7	6.6E+02	8.0E+06	5.7E+07
8	6.7E+02	8.2E+06	5.6E+07
9	6.7E+02	8.4E+06	4.8E+07
10	6.5E+02	8.1E+06	5.4E+07
11	6.2E+02	8.5E+06	5.2E+07
12	6.0E+02	8.9E+06	5.0E+07
13	5.9E+02	8.8E+06	5.1E+07
14	5.9E+02	9.5E+06	5.0E+07
15	6.1E+02	9.2E+06	4.9E+07
16	6.5E+02	8.4E+06	5.1E+07
17	6.5E+02	8.1E+06	4.7E+07
18	6.5E+02	8.1E+06	4.8E+07
19	6.3E+02	8.2E+06	4.8E+07
20	6.1E+02	8.3E+06	4.8E+07
21	6.2E+02	8.3E+06	4.9E+07
22	6.3E+02	8.7E+06	4.6E+07
23	6.4E+02	8.5E+06	5.1E+07
24	6.4E+02	8.4E+06	4.9E+07
25	6.6E+02	8.6E+06	3.5E+07
26	6.9E+02	9.2E+06	4.8E+07
27	6.7E+02	8.9E+06	4.8E+07
28	6.6E+02	8.4E+06	4.7E+07
29	6.6E+02	8.5E+06	3.3E+07
30	6.7E+02	8.8E+06	5.0E+07
31	6.8E+02	8.9E+06	3.8E+07



MICRON SEMICONDUCTOR LTD

02 AUG 2005

QUALITY CONTROL
QUALITY OFFICER
SIGNATURE

REMOVED

Resolution Plot

BB7

Wafer No.: **2435-2**

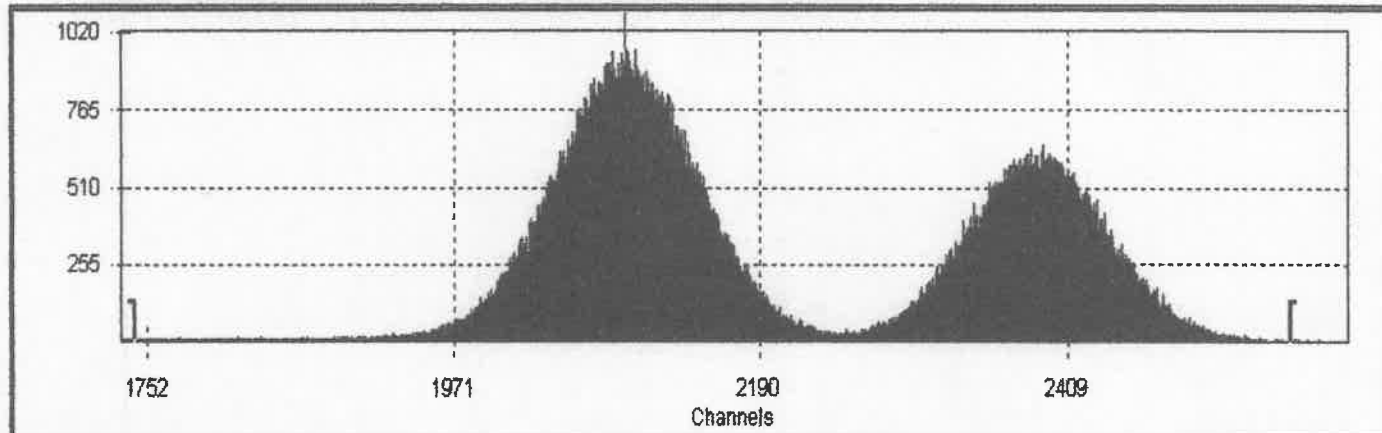
Thickness: **61** μm

JUNCTION

DET LINE: **308** KeV
SYSTEM: **284** KeV
CAL: **119** KeV

OHMIC

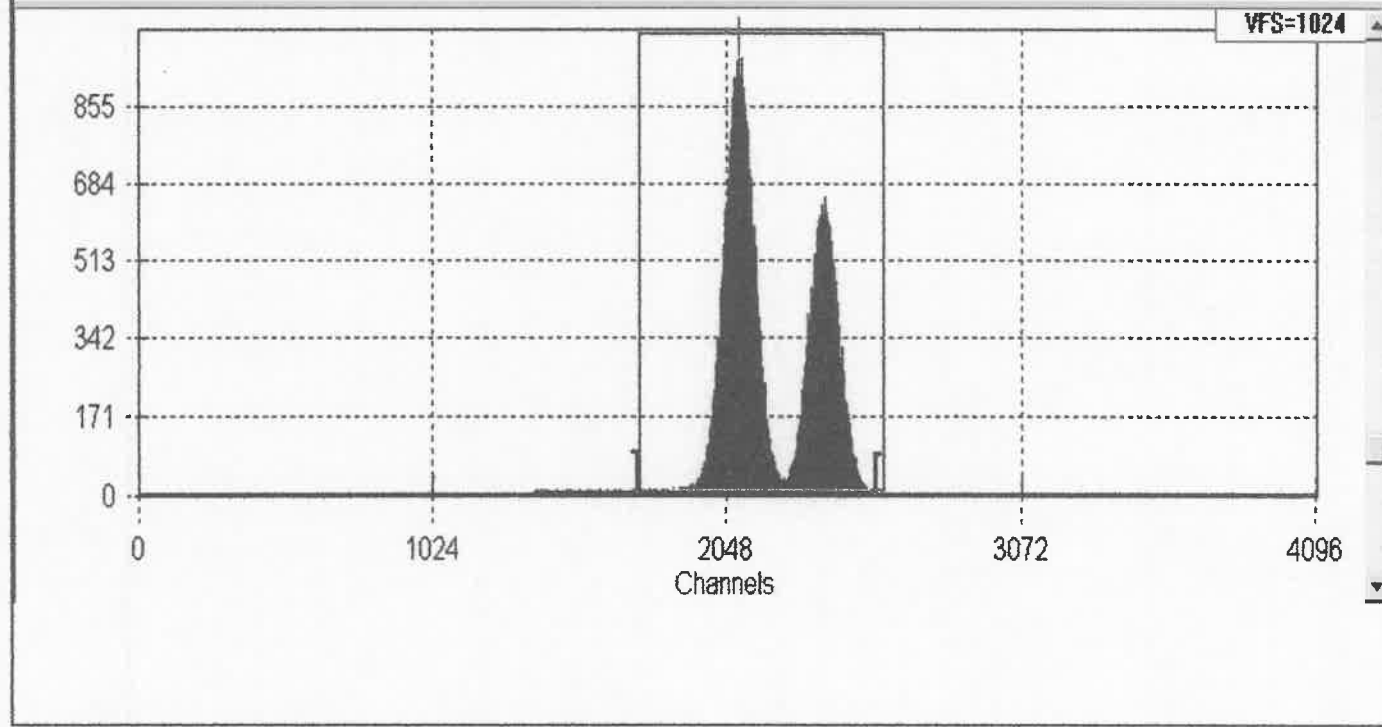
DET LINE: **310** KeV
SYSTEM: **284** KeV
CALC: **124** KeV



Source
Am 241

Rise Time
1

Flat Top
0



BIAS VOLTS= **8** V

Leakage **36** nA